

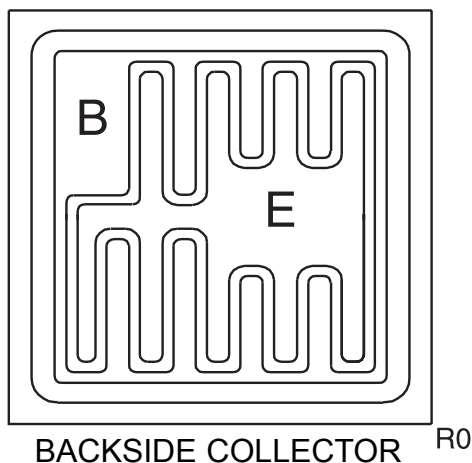
**PROCESS CP720**  
**Small Signal Transistor**  
PNP - High Current Transistor Chip

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	22 x 22 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	5.7 X 4.0 MILS
Emitter Bonding Pad Area	5.3 X 4.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

22,400

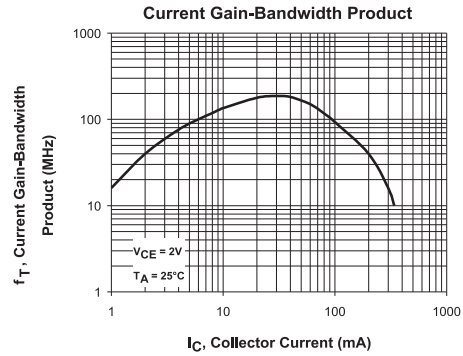
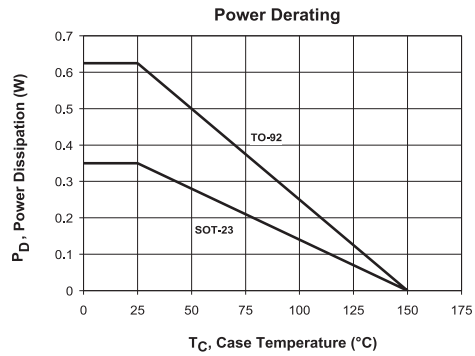
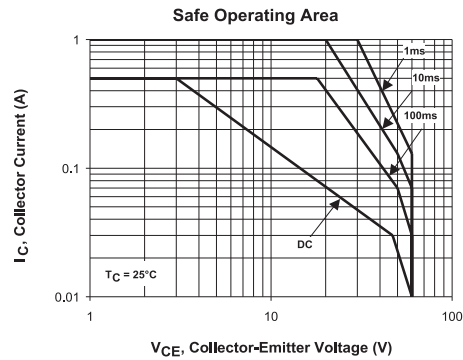
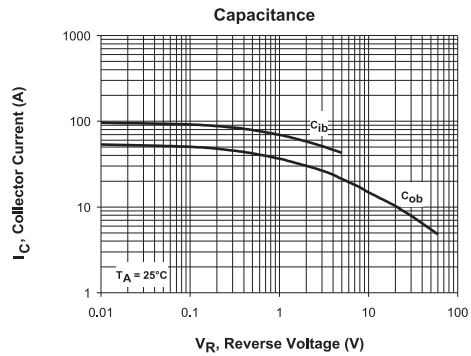
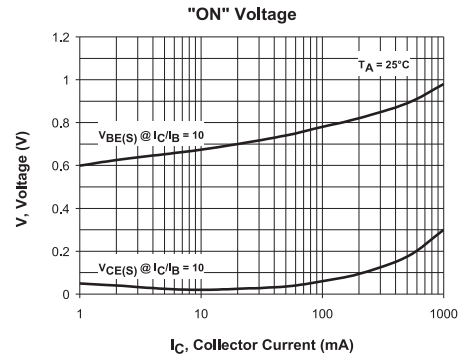
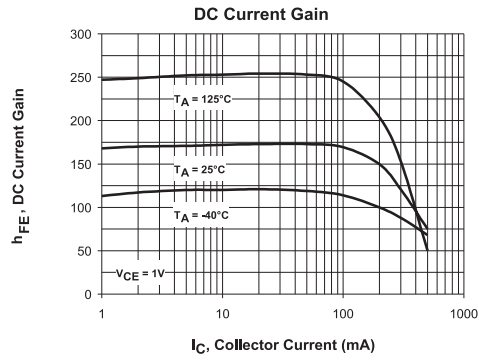
**PRINCIPAL DEVICE TYPES**

MPSA55

MPSA56

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